Short note on the density of states in 3D Weyl semimetals

K. Ziegler and A. Sinner

Institut für Physik, Universität Augsburg, D-86135 Augsburg, Germany

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The average density of states in a disordered three-dimensional Weyl system is discussed in the case of a continuous distribution of random scattering. Our results clearly indicate that the average density of states does not vanish, reflecting the absence of a critical point for a metal-insulator transition. This calculation supports recent suggestions of an avoided quantum critical point in the disordered three-dimensional Weyl semimetal. However, the effective density of states can be very small such that the saddle-approximation with a vanishing density of states might be valid for practical cases.

I. INTRODUCTION

The existence of a metal-insulator transition in disordered three-dimensional (3D) Weyl semimetals has been debated in the recent literature [1–11]. It is closely related to the question, whether or not the average density of states (DOS) at the spectral node vanishes below some critical disorder strength. The self-consistent Born approximation provides such a critical value with a vanishing DOS for weak disorder. It has been argued that rare regions of the random distribution may lead to a non-vanishing average DOS, though [1]. This was supported by recent numerical studies based on the T-matrix approach, which gives an exponentially small DOS [8] but was questioned in a recent study based on an instanton solution [11]. In this short note we show that, depending on the type and strength, a continuous distribution of disorder can create a substantial average DOS at the spectral node in 3D Weyl systems. This requires at least two impurities to create a resonant state between these impurities. A single impurity or a single instanton does not contribute to the spectral weight at the Weyl node, though, in accordance with the arguments in Ref. [11]. This supports the picture of an avoided quantum critical point in the presence of a distribution of impurities, as advocated in Ref. [8].

II. MODEL

The 3D Weyl Hamiltonian for electrons with momentum \vec{p} is expanded in terms of Pauli matrices τ_j $(j = 0, 1, 2, 3; \tau_0$ is the 2 × 2 unit matrix) as $H = H_0 - U\tau_0$, where

$$H_0 = v_F \vec{\tau} \cdot \vec{p} \quad \text{with} \quad \vec{\tau} = (\tau_1, \tau_2, \tau_3) \;.$$
 (1)

 v_F is the Fermi velocity and U is a disorder term, represented by a random potential with mean $\langle U \rangle = E_F$ (Fermi energy) and variance g. The average Hamiltonian $\langle H \rangle = H_0 - E_F \tau_0$ generates a spherical Fermi surface with radius $|E_F|$, and with electrons (holes) for $E_F > 0$ ($E_F < 0$). Physical quantities are expressed in such units that $v_F \hbar = 1$.

The DC limit $\omega \to 0$ of the conductivity of 3D Weyl fermions depends only on the scattering rate η and the Fermi energy E_F [7]:

$$\sigma(\eta, E_F) = 2\frac{e^2}{h}\eta^2 \int_0^\lambda \frac{(\eta^2 + k^2)^2 + E_F^2(2\eta^2 + 2k^2/3 + E_F^2)}{[(\eta^2 - E_F^2 + k^2)^2 + 4\eta^2 E_F^2]^2} \frac{k^2 dk}{2\pi^2}$$
(2)

with momentum cut-off λ . At the node ($E_F = 0$) the DC conductivity in Eq. (2) is reduced to the expression

$$\sigma = 2\frac{e^2}{h}\eta^2 \int_0^\lambda \frac{k^2}{(\eta^2 + k^2)^2} \frac{dk}{2\pi^2} = \frac{e^2\eta}{2\pi^2 h} \left[\arctan(1/\zeta) - \frac{\zeta}{1+\zeta^2} \right] \quad (\zeta = \eta/\lambda) , \tag{3}$$

which becomes for $\lambda \gg \eta$

$$\sigma \sim \frac{e^2}{4\pi h} \eta \ . \tag{4}$$



FIG. 1: Poles of the one-particle Green's function and the Cauchy-Lorentz distribution. The contour of the U_r -integration encloses only one pole of the Cauchy-Lorentz distribution but not the other poles.

The last result was also derived by Fradkin some time ago [12]. In contrast to the 2D case, where $\sigma = e^2/\pi h$, the 3D case gives a linearly increasing behavior with respect to the scattering rate.

The results in (2) - (4) clearly indicate that a metal-insulator transition in disordered 3D Weyl systems is directly linked to the scattering rate η . The latter describes the broadening of the poles of the oneparticle Green's function and is proportional to the average DOS

$$\rho_{\mathbf{r}}(E_F) = \lim_{\epsilon \to 0} \frac{1}{\pi} Im \left[\bar{G}_{\mathbf{rr}}(-i\epsilon) \right] , \quad \bar{G}(-i\epsilon) = \langle (H_0 - U\tau_0 - i\epsilon)^{-1} \rangle , \qquad (5)$$

where is \bar{G}_{rr} is the diagonal element of \bar{G} with respect to space coordinates. The self-consistent Born approximation [7, 12] at the node $E_F = 0$ reads

$$\eta = \eta I \text{ with } I = \gamma \left[\lambda - \eta \arctan(\lambda/\eta) \right]$$
 (6)

for the effective disorder strength $\gamma = g/2\pi^2$. There are two solutions, namely $\eta = 0$ and a solution with $\eta \neq 0$, which exists only for sufficiently large γ . Moreover, η vanishes continuously as we reduce γ . For $\eta \sim 0$ we obtain the linear behavior

$$\eta \sim \frac{2\lambda}{\pi} (\gamma \lambda - 1) , \qquad (7)$$

where $\gamma_c = 1/\lambda$ appears as a critical point with $\eta = 0$ for $\gamma \leq \gamma_c$ and $\eta > 0$ for $\gamma > \gamma_c$.

III. AVERAGE DENSITY OF STATES

A. Few impurities: Lippmann-Schwinger equation

At the node $E_F = 0$ the pure DOS $\rho_{0;\mathbf{r}}(E_F = 0)$ vanishes. However, a few impurities have already a significant effect on the local DOS: Assuming an impurity potential U_N on N sites, we use the identity (lattice version of the Lippmann-Schwinger equation)

$$(G_0^{-1} - U_N)^{-1} = G_0 + G_0 (1 - U_N P_N G_0 P_N)_N^{-1} U_N G_0 , \qquad (8)$$

where P_N is the projector on the impurity sites and $(...)_N^{-1}$ is the inverse on the impurity sites. Although $\rho_{0;\mathbf{r}}(E_F=0)$ vanishes, the second term on the right-hand side of Eq. (8) can contribute with the poles of $(\mathbf{1}-U_N P_N G_0 P_N)_N^{-1}$ to the DOS. These poles are "rare events" and require a fine-tuning of the impurity potential, whereas the generic case of a general U_N would still have a vanishing DOS. In a realistic situation the number of impurities is macroscopic with a non-zero density in the infinite system. Then the identity (8) cannot be used for practical calculations and we have to average over many impurity realizations. This leads to the average Green's function of Eq. (5), which will be calculated subsequently.

B. One vs. two impurities

The Green's function G_0 of the system without impurities reads

$$G_{0,\mathbf{r}}(-i\epsilon) = \frac{1}{|\mathcal{B}|} \int_{\mathcal{B}} \frac{e^{i\vec{k}\cdot\mathbf{r}}}{\epsilon^2 + k^2} \left(i\epsilon\tau_0 + \vec{k}\cdot\vec{\tau}\right) d^3k \equiv i\epsilon\gamma_0\tau_0 + \vec{\gamma}\cdot\vec{\tau} , \qquad (9)$$

where \mathcal{B} is the Brillouin zone of the underlying lattice and

$$\gamma_0 = \frac{1}{|\mathcal{B}|} \int_{\mathcal{B}} \frac{e^{i\vec{k}\cdot\mathbf{r}}}{\epsilon^2 + k^2} d^3k , \quad \gamma_j = \frac{1}{|\mathcal{B}|} \int_{\mathcal{B}} \frac{e^{i\vec{k}\cdot\mathbf{r}}k_j}{\epsilon^2 + k^2} d^3k \quad (j = 1, 2, 3) .$$

Then the diagonal element $G_{0,0} = i\epsilon\gamma\tau_0$ vanishes with $\epsilon \sim 0$. This implies that for a single impurity there is no bound state at finite impurity strength $U_{\mathbf{r}}$, since in the impurity term of the Lippmann-Schwinger equation (8) the 2 × 2 matrix

$$(\mathbf{1} - U_{\mathbf{r}} P_{\mathbf{r}} G_0 P_{\mathbf{r}})^{-1} = \frac{1}{1 - i\epsilon\gamma_0 U_{\mathbf{r}}} \tau_0 \tag{10}$$

has a pole at $U_{\mathbf{r}} \sim \infty$. The latter reflects the statement that a potential well in 3D Weyl semimetals does never generate spectral density at zero energy [11]. For two impurities, though, there is a resonant inter-site bound state between the impurities, since $G_{0,\mathbf{r}-\mathbf{r}'}$ ($\mathbf{r}' \neq \mathbf{r}$) does not vanish for $\epsilon \to 0$ but decays with a power law for $|\mathbf{r} - \mathbf{r}'|$ due to the Pauli matrix coefficients γ_j in Eq. (9):

$$(\mathbf{1} - UP_{\{\mathbf{r},\mathbf{r}'\}}G_0P_{\{\mathbf{r},\mathbf{r}'\}})^{-1} = \begin{pmatrix} 1 - i\epsilon\gamma_0 U_{\mathbf{r}} & 0 & -U_{\mathbf{r}}\gamma_3 & -U_{\mathbf{r}}(\gamma_1 - i\gamma_2) \\ 0 & 1 - i\epsilon\gamma_0 U_{\mathbf{r}} & -U_{\mathbf{r}}(\gamma_1 + i\gamma_2) & U_{\mathbf{r}}\gamma_3 \\ -U_{\mathbf{r}}\gamma_3 & -U_{\mathbf{r}}(\gamma_1 - i\gamma_2) & 1 - i\epsilon\gamma_0 U_{\mathbf{r}'} & 0 \\ -U_{\mathbf{r}'}(\gamma_1 + i\gamma_2) & U_{\mathbf{r}'}\gamma_3 & 0 & 1 - i\epsilon\gamma_0 U_{\mathbf{r}'} \end{pmatrix}^{-1}.$$
(11)

The degenerate eigenvalues of this matrix

$$\frac{1}{1 - i\epsilon\gamma_0(U_{\mathbf{r}} + U_{\mathbf{r}'})/2 \pm \sqrt{U_{\mathbf{r}}U_{\mathbf{r}'}(\gamma_1^2 + \gamma_2^2 + \gamma_3^2) - \epsilon^2\gamma_0^2(U_{\mathbf{r}} - U_{\mathbf{r}'})^2/4}}$$
(12)

have poles for finite $U_{\mathbf{r}}$, $U_{\mathbf{r}'}$. Thus, the corresponding bound states contribute with a non-vanishing density of states. In the remainder of the paper this result will be generalized to multiple impurities with corresponding resonant bound states.

C. Distribution with simple poles

From here on we consider a continuous distribution of the disorder potential U with $\prod_{\mathbf{r}} P(U_{\mathbf{r}}) dU_{\mathbf{r}}$ and average one-particle Green's function

$$\bar{G}(-i\epsilon) = \int (H_0 - U\tau_0 - i\epsilon)^{-1} \prod_{\mathbf{r}} P(U_{\mathbf{r}}) dU_{\mathbf{r}} .$$
(13)

For $\epsilon > 0$ the one-particle Green's function $(H_0 - U\tau_0 - i\epsilon)^{-1}$ has poles for $U_{\mathbf{r}}$ on the upper complex half-plane. Assuming that the distribution density $P(U_{\mathbf{r}})$ has isolated poles in the lower complex half-plane, the Cauchy integration can be applied by closing the integration along the real axis in the lower complex half-plane, as depicted in Fig. 1. The simplest realization is the Cauchy-Lorentz distribution

$$P_{CL}(U_{\mathbf{r}}) = \frac{1}{\pi} \frac{\eta}{(U_{\mathbf{r}} - E_F)^2 + \eta^2} , \qquad (14)$$

which gives

$$\bar{G}(-i\epsilon) = (H_0 - (E_F + i\epsilon + i\eta)\tau_0)^{-1} .$$
(15)



FIG. 2: Dividing the system into cubes $\{S\}$ of size |S| with boundary ∂S .

The average DOS then reads

$$\rho_{\mathbf{r}}(E_F) = \frac{\eta}{\pi} [(H_0 - E_F \tau_0)^2 + \eta^2 \tau_0]_{\mathbf{rr}}^{-1} .$$
(16)

The Cauchy-Lorentz distribution has an infinite second moment (i.e., g is infinite). A distributions with a finite second moment can be created from the differential of the Cauchy-Lorentz distribution with respect to η . Many distributions, like the popular Gaussian distribution

$$P_G(U_{\mathbf{r}}) = \frac{1}{\sqrt{\pi g}} e^{-(U_{\mathbf{r}} - E_F)^2/g} , \qquad (17)$$

do not have a simple pole structure, though. Then another approach can be applied to show that there is a non-vanishing average DOS.

D. Distribution without simple poles

Now we only assume that the distribution of $U_{\mathbf{r}}$ is continuous. Then the path of integration can also be deformed away from the poles of the Green's function to obtain a similar result as in the case of simple poles. The calculation would be more complex, though. Therefore, we use a different approach, whose main idea is to divide the system into cubes $\{S\}$ of finite identical size (cf. Fig. 2). Then we estimate (i) the average DOS inside an isolated cube and (ii) the contribution of the boundary ∂S between the cubes. This approach was used for a periodic lattice [13], for a random tight-binding model with symmetric Hamiltonian [14] and for two-dimensional Dirac fermions with random mass [15]. Later it was applied to S-wave superconductor with random order parameter [16], and to D-wave superconductor with random chemical potential [17].

For the average local DOS

$$\bar{\rho}_{\mathbf{r}} = \int \rho_{\mathbf{r}}(U) \prod_{\mathbf{r}} P(U_{\mathbf{r}}) dU_{\mathbf{r}}$$
(18)

we obtain from the estimation procedure with steps (i) and (ii) the inequality (cf. Supplemented Materials)

$$\sum_{\mathbf{r}\in S}\bar{\rho}_{\mathbf{r}} \geq \inf_{\{-a\leq U_{\mathbf{r}}'\leq a\}} \left[\int_{-v}^{v} \sum_{\mathbf{r}\in S} \rho_{S,\mathbf{r}}(U'+E) dE \inf_{-v\leq w\leq v} \prod_{\mathbf{r}\in S} P(U_{\mathbf{r}}'+w) \right] - \bar{P}_{S}|\partial S| , \qquad (19)$$

where |S| ($|\partial S|$) is the number of sites of S (∂S) and

$$\bar{P}_S = \inf_{\{-a \le U'_{\mathbf{r}} \le a\}, -v \le w \le v} \prod_{\mathbf{r} \in S} P(U'_{\mathbf{r}} + w) \ .$$

 $\bar{P}_S|\partial S|$ is the contribution of the boundary of a cube and the integral is the integrated DOS on a cube S. The boundary term is substracted because we have removed the boundary. In other words, the left-hand

side of (19) is the average DOS on the entire lattice, the right-hand side is the average DOS on the isolated cube S.

The value of the lower bound requires an adjustment of the still undetermined parameters a and v. The integrated DOS $\int_{-v}^{v} \sum_{\mathbf{r} \in S} \rho_{S,\mathbf{r}}(U' + E) dE$ on S is the number of eigenvalues on the interval [-v, v] of the S-projected Hamiltonian $H_0 - U'$. The projected Hamiltonian is an $|S| \times |S|$ Hermitean matrix with finite elements, whose eigenvalues are also finite. Thus, for a fixed a we can choose a sufficiently large v such that all eigenvalues of the projected Hamiltonian are inside the interval [-v, v]. In this case the integrated DOS is |S| and we get from (19) the inequality

$$\sum_{\mathbf{r}\in S}\bar{\rho}_{\mathbf{r}}\geq\bar{P}_{S}[|S|-|\partial S|].$$
(20)

S can always be chosen such that the size of the cube |S| is larger than the size $|\partial S|$ of its boundary. Then the right-hand side of (19) is strictly positive. v should not be too large, though, in order to avoid that \bar{P}_S becomes too small, assuming that a typical $P(U_{\mathbf{r}})$ decays for large values. The actual value of P_S depends on the distribution and can be exponentially small.

The average DOS of the entire lattice is estimated by the sum over all cubes, normalized by its number N. Since all cubes have the same lower bound, this sum is bounded by the right-hand side of (20). This indicates that our estimation works only for a macroscopic number of impurities, the case of a single impurity (10) would always give a lower bound zero.

IV. CONCLUSION

There is a crucial difference in terms of the average DOS: For a discrete distribution the average DOS is non-zero only if the disorder potential is "resonant" with the pure Green's function G_0 , according to the second term in Eq. (8). In particular, a single impurity fails to create spectral weight at the Weyl node. On the other hand, for a dense distribution of impurities, represented by a continuous random potential, there is always a non-vanishing average DOS due to inter-impurity bound states, provided that the values of $U_{\mathbf{r}}$ cover the entire spectrum of H_0 .

The existence of a critical disorder strength γ_c , as indicated by the self-consistent approximation in Eq. (7), contradicts the existence of a lower non-zero bound of the average DOS in Sect. III D. Therefore, the self-consistent calculation is not sufficiently accurate to describe the transport properties of the 3D Weyl semimetal properly. Since the lower bound of the average DOS is only a qualitative, although rigorous, estimation, still a reliable approximation is necessary to obtain an approximative value for the average DOS. The exact result obtained for the Cauchy-Lorentz distribution in Sect. III C gives only a hint, because this distribution is not generic. A possible option is a $N^{-\alpha}$ expansion with non-integer α [18].

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Supplementary Material: Short note on the density of states in 3D Weyl semimetals

K. Ziegler and A. Sinner

Institut für Physik, Universität Augsburg, D-86135 Augsburg, Germany

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I. LOWER BOUND OF THE AVERAGE DENSITY OF STATES

The main idea of calculating the DOS of an infinite system is to divide the large system into smaller (finite) cubes, calculate the DOS of these smaller cubes and estimate the contribution of the boundaries between them. This concept was developed for a periodic lattice by Ledermann [1]. Later it was extended to estimate the average DOS of a tight-binding model with random potential by Wegner [2], using the relation between the DOS and the integrated DOS. The calculational advantage of using a finite cube is its discrete spectrum. Then the corresponding DOS is a sum of Dirac Delta functions (or poles of the corresponding Green's function), which can be studied, for instance, by averaging with respect to a continuous disorder distribution. Then the Dirac Delta functions contribute to the average with their spectral weights.

This concept can be generalized by introducing a generating function for the local DOS, which is the phase of a unimodular function [3–5]. The phase has special properties under the change of the matrix elements of the underlying tight-binding Hamiltonian, which leads to a flexible method for estimating the average DOS.

For a diagonal matrix U and a short-range tight-binding matrix H_0 with lattice sites $\{\mathbf{r}\}$ there is a generating function

$$F_{\Lambda} = i \log \left[\frac{\det(H_0 - U - i\epsilon)}{\det(H_0 - U + i\epsilon)} \right] \quad \text{with } \rho_{\mathbf{r}} = \frac{1}{2\pi} \frac{\partial F_{\Lambda}}{\partial U_{\mathbf{r}}} \quad (\epsilon > 0)$$
(1)

for the local density of states $\rho_{\mathbf{r}}$ on the lattice Λ . The specific form of H_0 is not important for the following discussion, as long as it is short ranged. The latter is crucial because it allows us to obtain a sufficiently thin surface to disconnected cubes on the lattice Λ . Whether H_0 is a symmetric tight-binding Hamiltonian or a discrete Dirac operator with spinor states does not affect the validity of the approach.

 F_{Λ} has some remarkable properties: It is real, since the argument of the logarithm is unimodular, and it is an increasing function for any $U_{\mathbf{r}}$, since the DOS is non-negative. F_{Λ} is bounded for the shift of a single variable $U'_{\mathbf{r}} \to U_{\mathbf{r}}$ as

$$0 \le F_{\Lambda}(U_{\mathbf{r}}) - F_{\Lambda}(U_{\mathbf{r}}') \le 2\pi \quad (U_{\mathbf{r}} > U_{\mathbf{r}}')$$

$$\tag{2}$$

and for n shifted variables $U'_{\mathbf{r}_1}, U'_{\mathbf{r}_2}, ..., U'_{\mathbf{r}_n} \to U_{\mathbf{r}_1}, U_{\mathbf{r}_2}, ..., U_{\mathbf{r}_n}$ it is bounded as

$$0 \le F_{\Lambda}(U_{\mathbf{r}_{1}}, U_{\mathbf{r}_{2}}, ..., U_{\mathbf{r}_{n}}) - F_{\Lambda}(U'_{\mathbf{r}_{1}}, U'_{\mathbf{r}_{2}}, ..., U'_{\mathbf{r}_{n}}) \le 2\pi n \quad (U_{\mathbf{r}_{j}} > U'_{\mathbf{r}_{j}}) .$$
(3)

 F_{Λ} is additive on the lattice in the limit $U_{\mathbf{r}} \to \infty$ on ∂S :

$$\lim_{U_{\mathbf{r}}\to\infty, \mathbf{r}\in\partial S}F_{\Lambda} = F_S + F_{S''} \tag{4}$$

for a cube S with the boundary ∂S and the complement S'' outside $S \cup \partial S$. $F_S(F_{S''})$ is the function F_{Λ} with $H_0 - U \pm i\epsilon$ projected onto the subspace S(S''). The combination of (3) and (4) implies

$$F_S + F_{S''} - 2\pi |\partial S| \le F_\Lambda \le F_S + F_{S''} , \qquad (5)$$

where $|\partial S|$ is the number of lattice sites in ∂S .

Before we discuss the lower bound of the average DOS, an interpretation of the generating function F_{Λ} might be useful. According to its definition in Eq. (1) $F_{\Lambda}/2$ is the phase of the determinant of $H_0 - U - i\epsilon$. If we increase a single $U_{\mathbf{r}}$ this phase also increases, as indicated by (2). Since this happens for the increase of any of elements of U, the phase changes add up and the shift $U'_{\mathbf{r}_1}, U'_{\mathbf{r}_2}, ..., U'_{\mathbf{r}_n} \to U_{\mathbf{r}_1}, U_{\mathbf{r}_2}, ..., U'_{\mathbf{r}_n}$ provides a winding number of the determinant. The change of all elements of U by a constant E leads to the integrated DOS on the interval [0, E]:

$$N(0,E) = \int_0^E \sum_{\mathbf{r}} \rho_{\mathbf{r}} (U+y) dy , \qquad (6)$$

which is the number of eigenvalues of $H_0 - U$ on the interval [0, E]. In other words, the winding number of a global change of U is equal to the number of eigenstates on the interval of the change.

Now we return to the average DOS

$$\sum_{\mathbf{r}\in S} \bar{\rho}_{\mathbf{r}} := \sum_{\mathbf{r}\in S} \int \rho_{\mathbf{r}}(U) \prod_{\mathbf{r}\in\Lambda} P(U_{\mathbf{r}}) dU_{\mathbf{r}} = \frac{1}{2\pi} \int \sum_{\mathbf{r}\in S} \frac{\partial F_{\Lambda}}{\partial U_{\mathbf{r}}} \prod_{\mathbf{r}\in\Lambda} P(U_{\mathbf{r}}) dU_{\mathbf{r}} .$$
(7)

The distribution density on S can be written as an integral transform

$$\prod_{\mathbf{r}\in S} P(U_{\mathbf{r}}) = P'(U\Pi_S) \int_{-v}^{v} \prod_{\mathbf{r}\in S} P(U_{\mathbf{r}} - u) du , \qquad (8)$$

where Π_S is the projector onto S. This gives us for the right-hand side of (7)

$$\frac{1}{2\pi} \int \sum_{\mathbf{r}\in S} \frac{\partial F_{\Lambda}(U)}{\partial U_{\mathbf{r}}} \int_{-v}^{v} \prod_{\mathbf{r}\in S} P(U_{\mathbf{r}}-u) du P'(U\Pi_{S}) \prod_{\mathbf{r}\in S} dU_{\mathbf{r}} \prod_{\mathbf{r}\notin S} P(U_{\mathbf{r}}) dU_{\mathbf{r}}$$

and with the new integration variable $U'_{\mathbf{r}} = U_{\mathbf{r}} - u$ we have

$$= \frac{1}{2\pi} \int \int_{-v}^{v} \sum_{\mathbf{r} \in S} \frac{\partial F_{\Lambda}(U' + u\Pi_{S})}{\partial U_{\mathbf{r}}} P'((U' + u)\Pi_{S}) du \prod_{\mathbf{r} \in S} P(U'_{\mathbf{r}}) dU'_{\mathbf{r}} \prod_{\mathbf{r} \notin S} P(U_{\mathbf{r}}) dU_{\mathbf{r}}$$

$$\geq \frac{1}{2\pi} \int \inf_{-v \leq w \leq v} P'((U'+w)\Pi_S) \int_{-v}^{v} \sum_{\mathbf{r} \in S} \frac{\partial F_{\Lambda}(U'+u\Pi_S)}{\partial U_{\mathbf{r}}} du \prod_{\mathbf{r} \in S} P(U'_{\mathbf{r}}) dU'_{\mathbf{r}} \prod_{\mathbf{r} \notin S} P(U_{\mathbf{r}}) dU_{\mathbf{r}}$$
(9)

With the relation

$$\int_{-v}^{v} \sum_{\mathbf{r}\in S} \frac{\partial F_{\Lambda}(U'+u\Pi_{S})}{\partial U_{\mathbf{r}}} du = \int_{-v}^{v} \frac{\partial F_{\Lambda}(U'+u\Pi_{S})}{\partial u} du = F_{\Lambda}(U'+v\Pi_{S}) - F_{\Lambda}(U'-v\Pi_{S})$$

we obtain

$$\sum_{\mathbf{r}\in S}\bar{\rho}_{\mathbf{r}} \geq \frac{1}{2\pi} \int \left[F_{\Lambda}(U'+v\Pi_{S}) - F_{\Lambda}(U'-v\Pi_{S})\right] \inf_{-v \leq w \leq v} P'((U'+w)\Pi_{S}) \prod_{\mathbf{r}\in S} P(U'_{\mathbf{r}}) dU'_{\mathbf{r}} \prod_{\mathbf{r}\notin S} P(U_{\mathbf{r}}) dU_{\mathbf{r}} .$$
(10)

Now we apply the inequalities (5) and get a lower bound

$$\sum_{\mathbf{r}\in S} \bar{\rho}_{\mathbf{r}} \ge \frac{1}{2\pi} \int [F_S(U'+v) - F_S(U'-v) - 2\pi |\partial S|] \inf_{-v \le w \le v} P'((U'+w)\Pi_S) \prod_{\mathbf{r}\in S} P(U'_{\mathbf{r}}) dU'_{\mathbf{r}} , \qquad (11)$$

where the integration outside of S has been performed, since the integrand does not depend on $U_{\mathbf{r}}$ for $\mathbf{r} \notin S$. Next, we estimate the integral as

$$\frac{1}{2\pi} \int [F_S(U'+v) - F_S(U'-v) - 2\pi |\partial S|] \inf_{-v \le w \le v} P'((U'+w)\Pi_S) \prod_{\mathbf{r} \in S} P(U'_{\mathbf{r}}) dU'_{\mathbf{r}}$$

$$\geq \inf_{-a \le U'_{\mathbf{r}} \le a, \ \mathbf{r} \in S} [F_S(U'+v) - F_S(U'-v) - 2\pi |\partial S|] \frac{1}{2\pi} \inf_{-v \le w \le v} P'((U'+w)\Pi_S) . \tag{12}$$

 $F_S(U'+v) - F_S(U'-v)$ is the integrated DOS on the cube S

$$\int_{-v}^{v} \sum_{\mathbf{r} \in S} \rho_{S,\mathbf{r}} (U' + E) dE ,$$

which counts the number of eigenstates of the $|S| \times |S|$ -matrix $\Pi_S(H_0 - U')\Pi_S$ on the interval [-v, v]. Finally, from Eq. (8) we get

$$P'((U'+w)\Pi_S) = \frac{\prod_{\mathbf{r}\in S} P(U'_{\mathbf{r}}+w)}{\int_{-v}^{v} \prod_{\mathbf{r}\in S} P(U'_{\mathbf{r}}+w-u)du} \ge \prod_{\mathbf{r}\in S} P(U'_{\mathbf{r}}+w) , \qquad (13)$$

which gives inequality (19) of the Letter.

II. DERIVATION OF PROPERTIES (3) AND (4)

As discussed above, we obtain a lower bound of the average DOS essentially through properties (3) and (4) of the generating function F_{Λ} . These properties were discussed previously in Refs. [3]–[5] but for a consistent notation we summarize them in the following.

A. Property (3)

The inequality (2) for one shifted variable is directly related to the Lippmann-Schwinger equation for a single impurity via

$$F_{\Lambda}(U_{\mathbf{r}}') - F_{\Lambda}(U_{\mathbf{r}}'') = 2\pi \int_{U_{\mathbf{r}}''}^{U_{\mathbf{r}}'} \rho_{\mathbf{r}}(U_{\mathbf{r}}) dU_{\mathbf{r}} = -i \int_{U_{\mathbf{r}}''}^{U_{\mathbf{r}}'} \left[\frac{1}{1/\gamma_{\mathbf{r}}^* - U_{\mathbf{r}}} - \frac{1}{1/\gamma_{\mathbf{r}} - U_{\mathbf{r}}} \right] dU_{\mathbf{r}} \le 2\pi , \qquad (14)$$

where $\gamma_{\mathbf{r}} = G_{0,\mathbf{rr}}$ is the spatial diagonal element of the Green's function. The integral is also non-negative because the imaginary part of $\gamma_{\mathbf{r}}$ is positive for $\epsilon > 0$. A special case is that of Weyl particles because of $\gamma_{\mathbf{r}} \sim 0$. Then the above expression is always zero for finite $U_{\mathbf{r}}, U'_{\mathbf{r}}$ because the pole of the integrand is at infinity, as mention in the Letter.

Then we apply two times (14) to obtain for two shifted variables

$$0 \le F_{\Lambda}(U_{\mathbf{r}_{1}}, U_{\mathbf{r}_{2}}) - F_{\Lambda}(U'_{\mathbf{r}_{1}}, U'_{\mathbf{r}_{2}}) = F_{\Lambda}(U_{\mathbf{r}_{1}}, U_{\mathbf{r}_{2}}) - F_{\Lambda}(U'_{\mathbf{r}_{1}}, U_{\mathbf{r}_{2}}) + F_{\Lambda}(U'_{\mathbf{r}_{1}}, U_{\mathbf{r}_{2}}) - F_{\Lambda}(U'_{\mathbf{r}_{1}}, U'_{\mathbf{r}_{2}}) \le 4\pi$$

This procedure can be repeated n times for n shifted variables to give (3). The result is justified by complete induction: Suppose (3) is correct. Then we get for n + 1

$$F_{\Lambda}(U_{\mathbf{r}_{1}}, U_{\mathbf{r}_{2}}, ..., U_{\mathbf{r}_{n+1}}) - F_{\Lambda}(U'_{\mathbf{r}_{1}}, U'_{\mathbf{r}_{2}}, ..., U'_{\mathbf{r}_{n+1}}) = F_{\Lambda}(U_{\mathbf{r}_{1}}, U_{\mathbf{r}_{2}}, ..., U_{\mathbf{r}_{n+1}}) - F_{\Lambda}(U'_{\mathbf{r}_{1}}, U'_{\mathbf{r}_{2}}, ..., U'_{\mathbf{r}_{n}}, U_{\mathbf{r}_{n+1}})$$

$$+F_{\Lambda}(U'_{\mathbf{r}_{1}},U'_{\mathbf{r}_{2}},...,U'_{\mathbf{r}_{n}},U_{\mathbf{r}_{n+1}})-F_{\Lambda}(U'_{\mathbf{r}_{1}},U'_{\mathbf{r}_{2}},...,U'_{\mathbf{r}_{n}},U'_{\mathbf{r}_{n+1}}) \leq 2\pi n+2\pi = 2\pi(n+1) .$$

B. Property (4)

The relation (4) can be derived by splitting $U = U_{S \cup S''} + U_{\partial S}$ with the projectors Π_S , $\Pi_{S''}$ and $\Pi_{\partial S}$ onto S, S'' and ∂S , respectively:

$$U_{S\cup S''} = \Pi_S U \Pi_S + \Pi_{S''} U \Pi_{S''} - \Pi_S - \Pi_{S''} , \quad U_{\partial S} = \Pi_{\partial S} U \Pi_{\partial S} + \Pi_S + \Pi_{S''} .$$

Then we obtain the following equations

$$\frac{\det(H_0 - U - i\epsilon)}{\det(H_0 - U + i\epsilon)} = \frac{\det(H_0 - U_{S \cup S''} - U_{\partial S} - i\epsilon)}{\det(H_0 - U_{S \cup S''} - U_{\partial S} + i\epsilon)}$$

$$=\frac{\det\{U_{\partial S}^{1/2}[U_{\partial S}^{-1/2}(H_0 - U_{S \cup S''} - i\epsilon)U_{\partial S}^{-1/2} - \mathbf{1}]U_{\partial S}^{1/2}\}}{\det\{U_{\partial S}^{1/2}[U_{\partial S}^{-1/2}(H_0 - U_{S \cup S''} + i\epsilon)U_{\partial S}^{-1/2} - \mathbf{1}]U_{\partial S}^{1/2}\}} = \frac{\det[U_{\partial S}^{-1/2}(H_0 - U_{S \cup S''} - i\epsilon)U_{\partial S}^{-1/2} - \mathbf{1}]}{\det[U_{\partial S}^{-1/2}(H_0 - U_{S \cup S''} + i\epsilon)U_{\partial S}^{-1/2} - \mathbf{1}]}.$$
(15)

The limit $U_{\mathbf{r}} \to \infty$ on ∂S gives

$$\lim_{U_{\mathbf{r}}\to\infty, \ \mathbf{r}\in\partial S} U_{\partial S}^{-1/2} = \Pi_S + \Pi_{S''} \ . \tag{16}$$

Since ∂S separates two regions S and S'' on the lattice with $\Pi_S H_0 \Pi_{S''} = 0$, this leads to

$$\lim_{U_{\mathbf{r}}\to\infty, \ \mathbf{r}\in\partial S} U_{\partial S}^{-1/2} (H_0 - U_{S\cup S''} \pm i\epsilon) U_{\partial S}^{-1/2} = (\Pi_S + \Pi_{S''}) (H_0 - U_{S\cup S''} \pm i\epsilon) (\Pi_S + \Pi_{S''})$$

and, because of $\Pi_S H_0 \Pi_{S''} = 0$, we get

$$= \Pi_{S}(H_{0} - U \pm i\epsilon)\Pi_{S} + \Pi_{S''}(H_{0} - U \pm i\epsilon)\Pi_{S''} .$$
(17)

For the ratio of determinants we have

$$\lim_{U_{\mathbf{r}}\to\infty,\ \mathbf{r}\in\partial S}\frac{\det(H_0-U-i\epsilon)}{\det(H_0-U+i\epsilon)} = \frac{\det_S(H_0-U-i\epsilon)}{\det_S(H_0-U+i\epsilon)}\frac{\det_{S''}(H_0-U-i\epsilon)}{\det_{S''}(H_0-U+i\epsilon)},$$
(18)

where the index of the determinants refers to the projection of the matrix. Inserting this result into F_{Λ} gives Eq. (4).

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